











SN74CBTLV3253

ZHCSHG4J-DECEMBER 1997-REVISED JANUARY 2018

SN74CBTLV3253 低电压、双 4 选 1 FET 多路复用器/多路信号分离器

1 特性

- 在功能上与 QS3253 等效
- 两个端口间使用 5Ω 开关连接
- 数据 I/O 端口上的轨至轨开关
- Ioff 支持局部关断模式运行
- 锁断性能超过 100mA,符合 JESD 78 Ⅱ 类规范的 要求

2 应用

- 视频广播:基于 IP 的多格式转码器
- 视频通信系统

3 说明

SN74CBTLV3253 器件是一款双 4 选 1 高速 FET 多路复用器和多路信号分离器。此开关具有低导通状态电阻,可以在最短传播延迟情况下建立连接。

选择 (S0, S1) 输入端控制数据流。当相关输出使能 (OE) 输入为高电平时,FET 多路复用器/多路信号分离器被禁用。

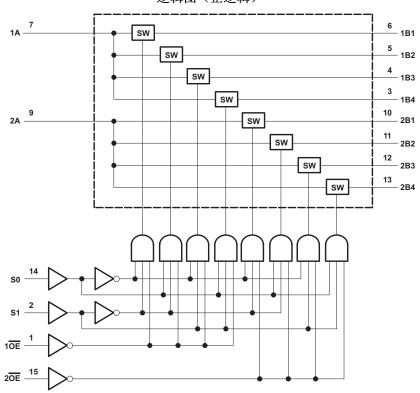
SN74CBTLV3253 器件完全 适用于 使用 I_{off} 的局部掉电应用。I_{off} 特性确保在关断时防止损坏电流通过器件回流。该器件可在关断时提供隔离。

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74CBTLV3253D	SOIC (16)	9.90mm × 3.90mm
SN74CBTLV3253DBQ	SSOP (16)	4.90mm × 3.90mm
SN74CBTLV3253DGV	TVSOP (16)	3.60mm × 4.40mm
SN74CBTLV3253RGY	VQFN (16)	4.00mm × 3.50mm
SN74CBTLV3253PW	TSSOP (16)	5.00 mm × 4.40 mm

 For all available packages, see the orderable addendum at the end of the data sheet.

逻辑图 (正逻辑)



Changes from Revision F (July 2012) to Revision G

Page

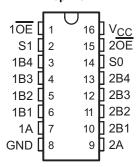


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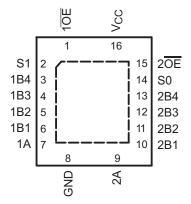


5 Pin Configuration and Functions

D, DBQ, DGV, or PW Package 16-Pin SOIC, SSOP, TVSOP, or TSSOP Top View



RGY Package 16-Pin VQFN Top View



Pin Functions

Р	PIN		DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
1 OE	1	I	Output Enable 1 Active-Low
S1	2	I	Select Pin 1
1B4	3	I/O	Channel 1 I/O 4
1B3	4	I/O	Channel 1 I/O 3
1B2	5	I/O	Channel 1 I/O 2
1B1	6	I/O	Channel 1 I/O 1
1A	7	I/O	Channel 1 common
GND	8	_	Ground
2A	9	I/O	Channel 2 common
2B1	10	I/O	Channel 2 I/O 1
2B2	11	I/O	Channel 2 I/O 2
2B3	12	I/O	Channel 2 I/O 3
2B4	13	I/O	Channel 2 I/O 4
S0	14	I	Select Pin 0
2 OE	15	I	Output Enable 2 Active-Low
V _{CC}	16	_	Power



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V_{CC}	Supply voltage		-0.5	4.6	٧
V_{IN}	Control input voltage (2)		-0.5	4.6	٧
V _{I/O}	Switch I/O voltage ⁽²⁾		-0.5	4.6	V
I _{IK}	Control input clamp current	V _{IN} < 0		- 50	mA
I _{I/OK}	I/O port clamp current	V _{I/O} < 0		- 50	mA
	Continuous current through V _{CC} or GND			±128	mA
TJ	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
Floatroatatio		Human Body Model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	+2000	V
V _{ESD}	Electrostatic discharge	Charged-Device Model (CDM), per JEDEC specification JESD22-C101, all pins (2)	+1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		2.3	3.6	V
V _{IH} High-level control input voltage	V _{CC} = 2.3 V to 2.7 V	1.7			
	High-level control input voltage	In-level control input voltage $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		V
	Laurel and the line of the sec	V _{CC} = 2.3 V to 2.7 V		0.7	\ <i>/</i>
V _{IL} Low-level control input vo	Low-level control input voltage	V _{CC} = 2.7 V to 3.6 V		0.8	V
T _A	Operating free-air temperature		-40	85	°C

⁽¹⁾ All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

6.4 Thermal Information

		SN74CBTLV3253					
	THERMAL METRIC ⁽¹⁾	D (SOIC)	DBQ (SSOP)	DGV (TVSOP)	PW (TSSOP)	RGY (VQFN)	UNIT
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	86.7	112.4	123.1	110.9	47.1	°C/W
R _{θJC(to}	Junction-to-case (top) thermal resistance	47.8	63.6	48.7	45.8	58.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.7	54.8	54.9	56.0	24.0	°C/W
ΨЈТ	Junction-to-top characterization parameter	12.3	17.0	5.2	5.4	1.8	°C/W
ΨЈВ	Junction-to-board characterization parameter	43.5	54.4	54.3	55.4	24.0	°C/W
R _{θJC(b} ot)	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	n/a	9.6	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARA	AMETER		TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
V_{IK}		$V_{CC} = 3 V$,	I _I = -18 mA				-1.2	V
I _I		$V_{CC} = 3.6 \text{ V},$	$V_I = V_{CC}$ or GND				±1	μΑ
I _{off}		$V_{CC} = 0$,	V_{I} or $V_{O} = 0$ to 3.6 V				15	μΑ
I _{CC}		V _{CC} = 3.6 V,	I _O = 0,	$V_I = V_{CC}$ or GND			10	μΑ
ΔI _{CC} ⁽²⁾	Control inputs	V _{CC} = 3.6 V,	One input at 3 V,	Other inputs at V _{CC} or GND			300	μΑ
C _i	Control inputs	V _I = 3 V or 0				3		pF
<u> </u>	A port	V 2.V or 0	ŌĒ = V _{CC}			20.5		~F
C _{io(OFF)}	B port	$V_0 = 3 \text{ V or } 0,$	OE = VCC			5.5		pF
			V 0	I _I = 64 mA		5	8	
		$V_{CC} = 2.3 \text{ V},$ TYP at $V_{CC} = 2.5 \text{ V}$	$V_I = 0$	I _I = 24 mA		5	8	
. (3)		111 at voc = 2.5 v	V _I = 1.7 V,	I _I = 15 mA		27	40	0
r _{on} (3)			., .	I _I = 64 mA		5	7	Ω
		$V_{CC} = 3 V$	$V_I = 0$	I _I = 24 mA		5	7	
			V _I = 2.4 V,	I _I = 15 mA		10	15	

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM	TO (OUTPUT)	V _{CC} = 2. ± 0.2	.5 V V	V _{CC} = 3 ± 0.3	.3 V V	UNIT
	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	
	A or B ⁽¹⁾	B or A		0.15		0.25	
t _{pd}	S	A or B	1	6.8	1	5.5	ns
t _{en}	S	A or B	1	4.3	1	4	ns
t _{dis}	S	A or B	1	5.1	1	5.5	ns
t _{en}	ŌĒ	A or B	1	5	1	4.8	ns
t _{dis}	ŌĒ	A or B	1	5.5	1	5.4	ns

⁽¹⁾ The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C. This is the increase in supply current for each input that is at the specified voltage level, rather than V_{CC} or GND.

Measured by the voltage drop between the A and the B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.



6.7 Typical Characteristics

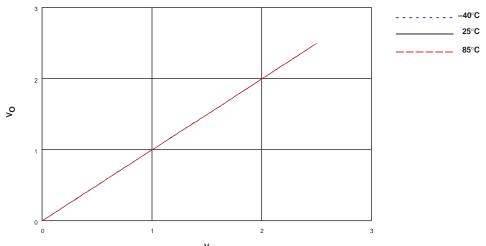
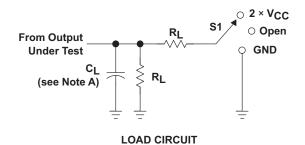


Figure 1. V_0 vs V_1 , V_{CC} = 2.5 V

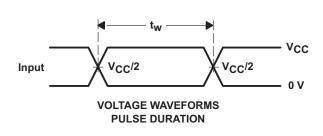


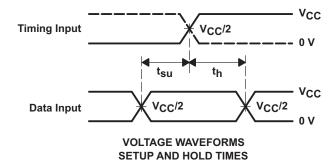
7 Parameter Measurement Information

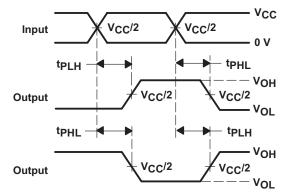


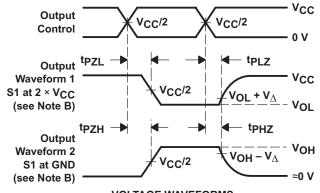
TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	2 × V _{CC}
tPHZ/tPZH	GND

V _{CC}	CL	RL	${f v}_{\!\Delta}$
2.5 V ±0.2 V	30 pF	500 Ω	0.15 V
3.3 V ±0.3 V	50 pF	500 Ω	0.3 V









VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS

VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

Figure 2. Test Circuit and Voltage Waveforms



8 Detailed Description

8.1 Overview

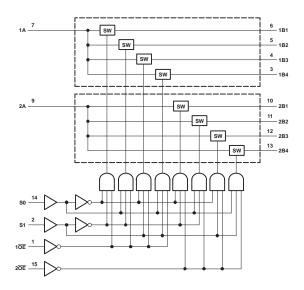
The SN74CBTLV3253 device is a dual 1-of-4 high-speed FET multiplexer/demultiplexer. The low ON-state resistance of the switch allows connections to be made with minimal propagation delay.

The select (S0, S1) inputs control the data flow. The FET multiplexers and demultiplexers are disabled when the associated output-enable (\overline{OE}) input is high.

The SN74CBTLV3253 device is fully specified for partial-power-down applications using I_{off} . The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram



8.3 Feature Description

The SN74CBTLV3253 device is functionally equivalent to the QS3253 and has a 5- Ω switch connection between two ports

It also has rail-to-rail switching on data I/O ports as well as I_{off} supporting partial-power-down mode operation

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74CBTLV3253.

Table 1. Function Table (Each Multiplexer/Demultiplexer)

	INPUTS	FUNCTION	
ŌĒ	S 1	S0	FUNCTION
L	L	L	A port = B1 port
L	L	Н	A port = B2 port
L	Н	L	A port = B3 port
L	Н	Н	A port = B4 port
Н	X	X	Disconnect



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74CBTLV3253 can be used to multiplex and demultiplex up to 2 channels simultaneously in a 4:1 configuration. The application shown here is a 2-bit bus being multiplexed between two devices. the OE and S pins are used to control the chip from the bus controller. This is a very generic example, and could apply to many situations.

9.2 Typical Application

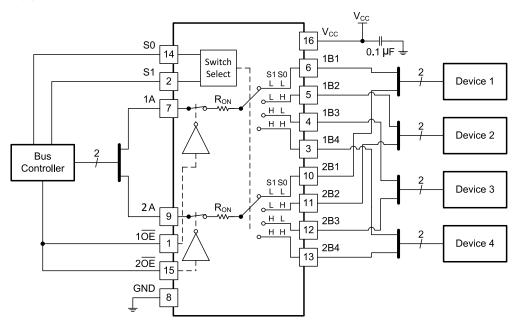


Figure 3. Typical Application of the SN74CBTLV3253

9.2.1 Design Requirements

The 0.1µF capacitor should be placed as close as possible to the device.

9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
 - For specified high and low levels, see V_{IH} and V_{IL} in Recommended Operating Conditions.
 - Inputs and outputs are overvoltage tolerant slowing them to go as high as 4.6 V at any valid V_{CC}.
- 2. Recommended Output Conditions:
 - Load currents should not exceed ±128 mA per channel.
- 3. Frequency Selection Criterion:
 - Added trace resistance/capacitance can reduce maximum frequency capability; use layout practices as directed in Layout.



Typical Application (continued)

9.2.3 Application Curve

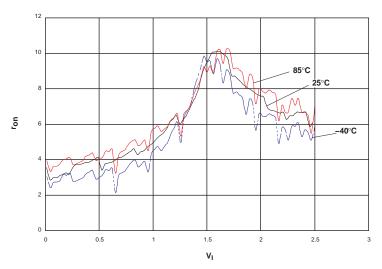


Figure 4. r_{on} vs V_{I} , $V_{CC} = 2.5 \text{ V}$

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions* table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μF bypass capacitor is recommended. If multiple pins are labeled V_{CC} , then a 0.01- μF or 0.022- μF capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μF bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 μF and 1 μF are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.



11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 5 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

11.2 Layout Example

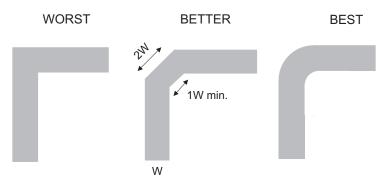


Figure 5. Trace Example



12 器件和文档支持

12.1 Documentation Support

12.1.1 相关文档

请参阅如下相关文档:

《CMOS 输入缓慢变化或悬空的影响》, SCBA004

12.2 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商"按照原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点;请参阅 TI 的 《使用条款》。

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设计支持 TI 参考设计支持 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

12.3 商标

E2E is a trademark of Texas Instruments.

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12.4 静电放电警告



这些装置包含有限的内置 ESD 保护。 存储或装卸时,应将导线一起截短或将装置放置于导电泡棉中,以防止 MOS 门极遭受静电损伤。

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更, 恕不另行通知和修 订此文档。如欲获取此数据表的浏览器版本,请参阅左侧的导航。 www.ti.com 2-May-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
part namber	(1)	(2)			(3)	(4)	(5)		(6)
SN74CBTLV3253D	Obsolete	Production	SOIC (D) 16	-	-	Call TI	Call TI	-40 to 85	CBTLV3253
SN74CBTLV3253DBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL253
SN74CBTLV3253DGVR	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL253
SN74CBTLV3253DR	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3253
SN74CBTLV3253PW	Obsolete	Production	TSSOP (PW) 16	-	-	Call TI	Call TI	-40 to 85	CL253
SN74CBTLV3253PWR	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL253
SN74CBTLV3253RGYR	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL253

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS WHO SHOPE THE STATE OF THE

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CBTLV3253DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CBTLV3253DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CBTLV3253DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74CBTLV3253PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3253RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1



www.ti.com 14-Dec-2024



*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN74CBTLV3253DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0	
SN74CBTLV3253DGVR	TVSOP	DGV	16	2000	367.0	367.0	35.0	
SN74CBTLV3253DR	SOIC	D	16	2500	353.0	353.0	32.0	
SN74CBTLV3253PWR	TSSOP	PW	16	2000	367.0	367.0	35.0	
SN74CBTLV3253RGYR	VQFN	RGY	16	3000	367.0	367.0	35.0	

D (R-PDS0-G16)

PLASTIC SMALL OUTLINE



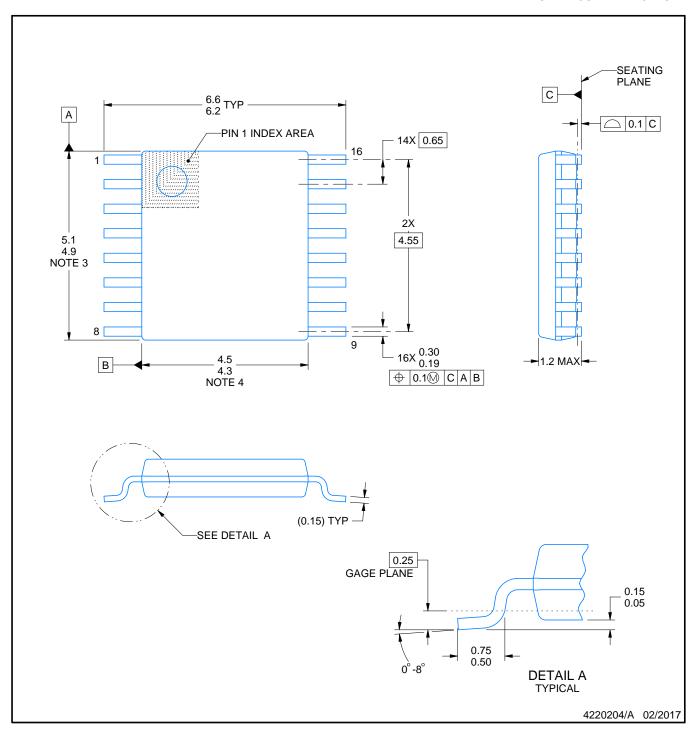
NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.





SMALL OUTLINE PACKAGE



NOTES:

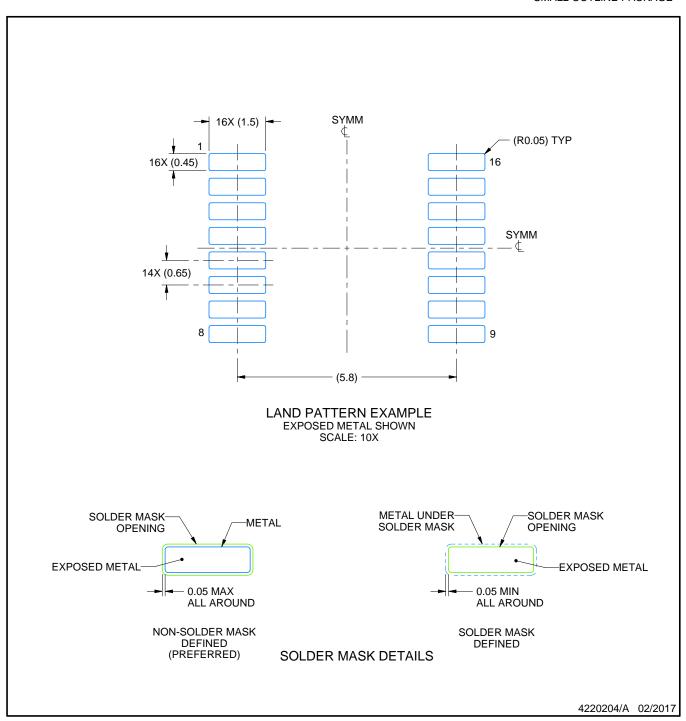
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



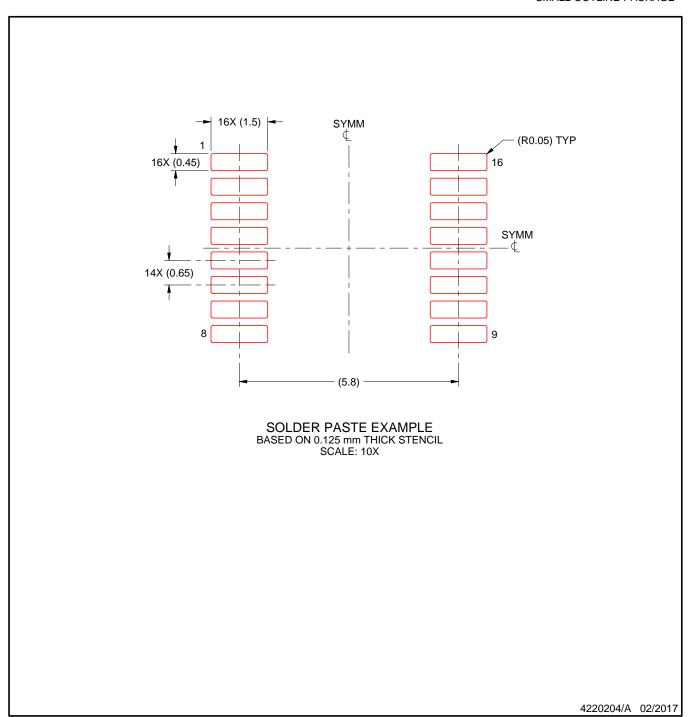
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



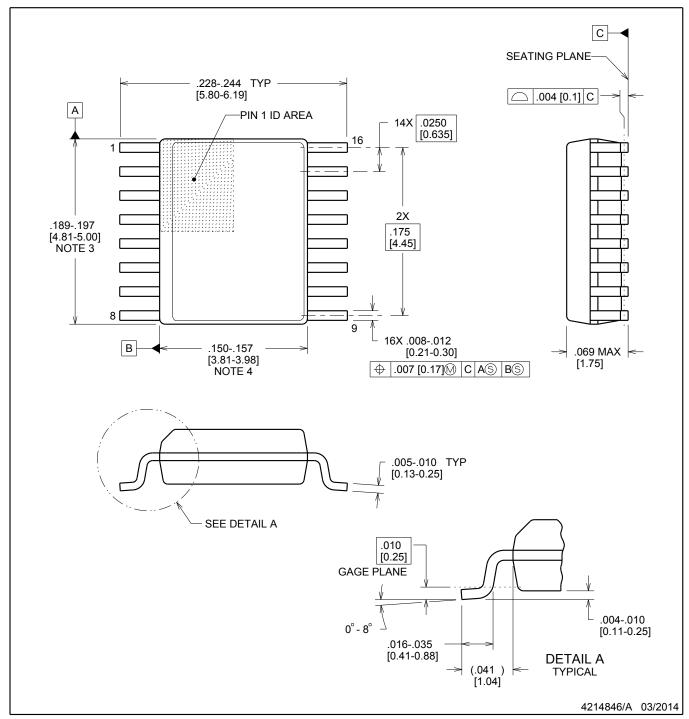
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SHRINK SMALL-OUTLINE PACKAGE

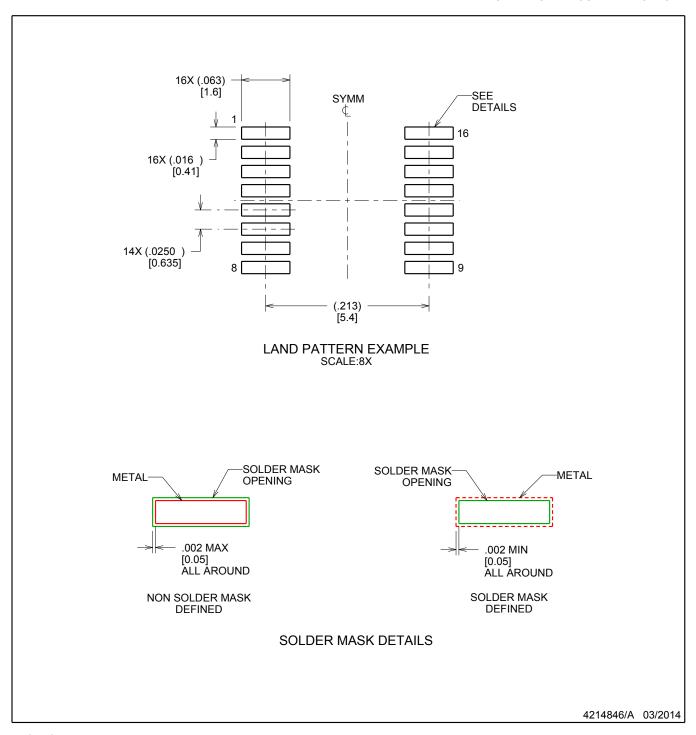


NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MO-137, variation AB.



SHRINK SMALL-OUTLINE PACKAGE



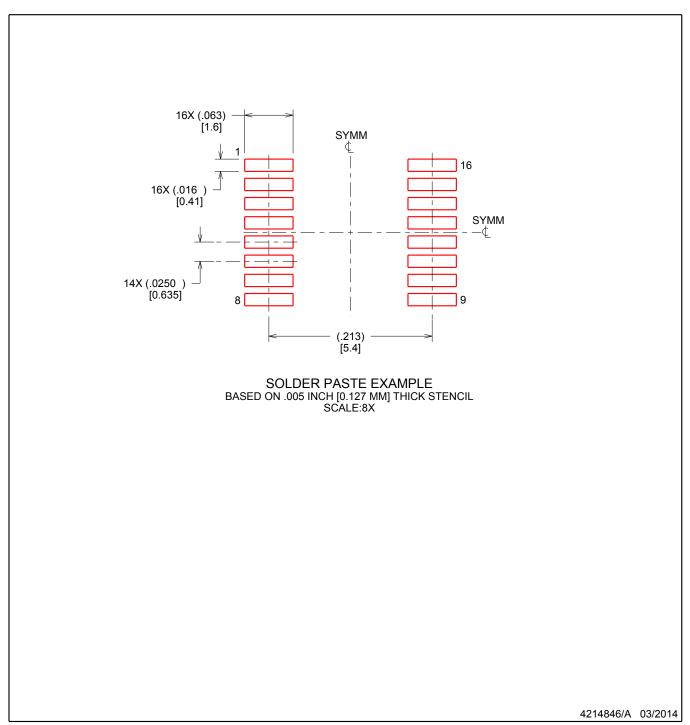
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



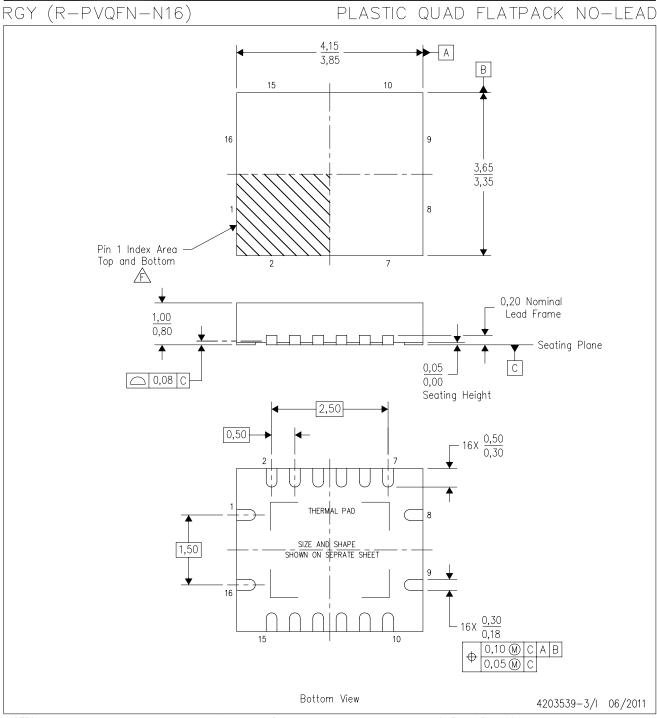
SHRINK SMALL-OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO-241 variation BA.



RGY (R-PVQFN-N16)

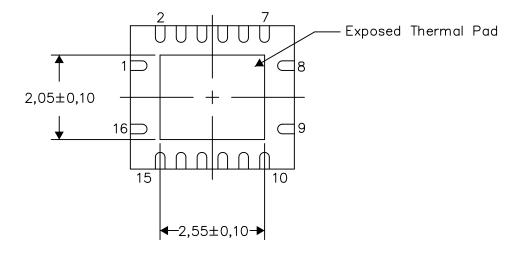
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

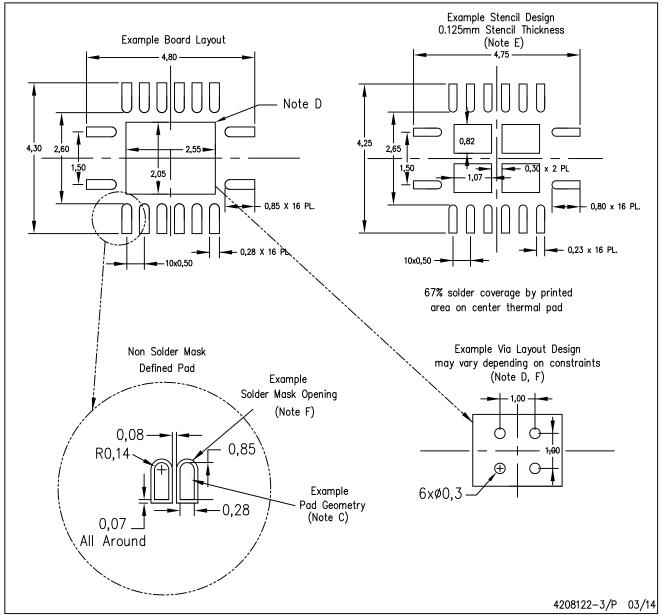
4206353-3/P 03/14

NOTE: All linear dimensions are in millimeters



RGY (R-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



NOTES:

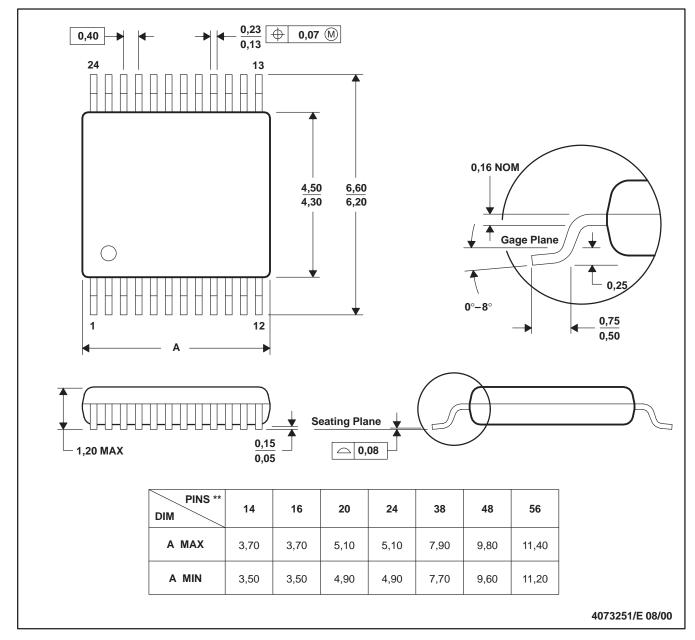
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



DGV (R-PDSO-G**)

24 PINS SHOWN

PLASTIC SMALL-OUTLINE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.

D. Falls within JEDEC: 24/48 Pins – MO-153 14/16/20/56 Pins – MO-194

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